RClamp3344T Low Voltage RailClamp® 4-Line ESD Protection

PROTECTION PRODUCTS - RailClamp®

Description

RClamp®3344T is a low voltage RailClamp which can provide ESD protection to IEC 61000-4-2 on high-speed ports. It is manufactured using Semtech's proprietary low voltage technology, designed to minimize both the ESD peak clamping and TLP clamping voltage. These devices "snap-back" to a low on-state voltage when the breakdown voltage of the device is exceeded. This has the advantage of lowering the overall ESD clamping voltage. When the device is in the on-state, the dynamic resistance is typically 0.30 Ohms, further minimizing the ESD clamping. Maximum capacitance is only 0.35pF allowing the RClamp3344T to be used in applications operating in excess of 6GHz without appreciable signal attenuation. Each device will protect four lines operating at 3.3 volts.

RClamp3344T is in a 5-pin SLP1308N5T package. It measures 1.3×0.8 mm with a nominal height of 0.40mm. The innovative flow through package design simplifies pcb layout and allows matched trace lengths for consistant impedance between high speed differential lines.

The combination of low peak ESD clamping, low dynamic resistance, and innovative package design enables this device to provide the highest level of ESD protection for applications such as USB 3.0, MIPI/MDDI, and LVDS lines.

Features

- ♦ High ESD withstand Voltage: +/-17kV (Contact), +/-20kV (Air) per IEC 61000-4-2
- ◆ Package design optimized for high speed lines
- Protects four high-speed lines
- Flow-Through design
- Low capacitance: 0.35pF Maximum
 Dynamic Resistance: 0.30 Ohms Typical
- ◆ Low ESD clamping voltage
- Operating voltage: 3.3V
- ◆ Solid-state silicon-avalanche technology

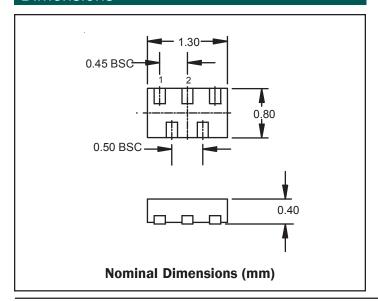
Mechanical Characteristics

- ◆ SLP1308N5T 5-pin package (1.3 x 0.8 x 0.40mm)
- ◆ Pb-Free, Halogen Free, RoHS/WEEE Compliant
- ◆ Lead finish: NiPdAu
- Marking: Marking Code
- ◆ Packaging: Tape and Reel

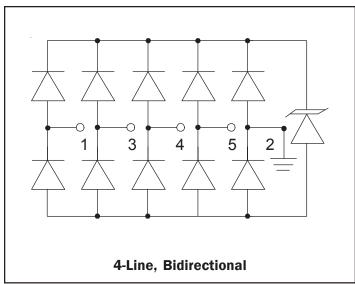
Applications

- ◆ USB 3.0
- ◆ V-By-One
- ◆ LVDS
- ◆ MIPI/MDDI
- MyDP

Dimensions



Schematic & PIN Configuration





Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Current (tp = 8/20µs)	I _{PP}	4	А
ESD per IEC 61000-4-2 (Air) ¹ ESD per IEC 61000-4-2 (Contact) ¹	V _{ESD}	+/- 20 +/- 17	kV
Operating Temperature	T _J	-40 to +85	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (T=25°C Unless Otherwise Specified)

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}	Any I/O to GND			3.3	V
Breakdown Voltage	$V_{_{BR}}$	I _{BR} = 10μΑ	7.5	8.8	9.8	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3V, T=25°C Any I/O to GND		0.01	0.05	μΑ
Clamping Voltage	V _c	I _{PP} = 1A, tp = 8/20µs Any I/O to GND		3.5	5	V
Clamping Voltage	V _c	I _{PP} = 4A, tp = 8/20µs Any I/O to GND		5	6.5	V
ESD Clamping Voltage ²	V _c	I _{pp} = 16A, tlp = 0.2/100ns		9.5		V
ESD Clamping Voltage ²	V _c	I _{pp} = -16A, tIp = 0.2/100ns		9.5		V
Dynamic Resistance (Positive) ^{2,3}	R _D	tlp = 0.2/100ns		0.30		Ohms
Dynamic Resistance (Negative) ^{2,3}	R _D	tlp = 0.2/100ns		0.30		Ohms
Junction Capacitance	C _j	V _R = 0V, f = 1MHz, Any I/O to GND		0.30	0.35	pF

Notes

¹⁾Measured with a 20dB attenuator, 50 Ohm scope input impedance, 2GHz bandwidth. ESD gun return path connected to ESD ground plane.

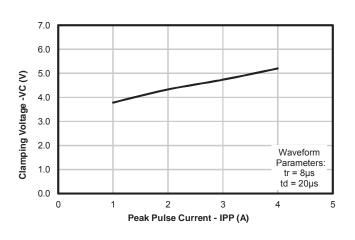
²⁾Transmission Line Pulse Test (TLP) Settings: $t_p = 100$ ns, $t_r = 0.2$ ns, I_{TLP} and V_{TLP} averaging window: $t_1 = 70$ ns to $t_2 = 90$ ns. Parameters guaranteed by design.

³⁾ Dynamic resistance calculated from $I_{TIP} = 4A$ to $I_{TIP} = 16A$

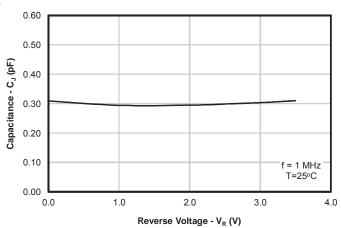


Typical Characteristics

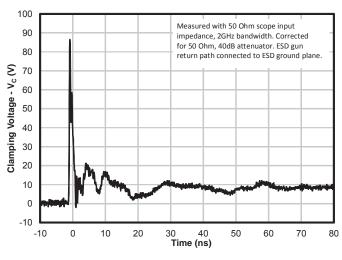
Clamping Voltage vs. Peak Pulse Current (Between any I/O and Ground)



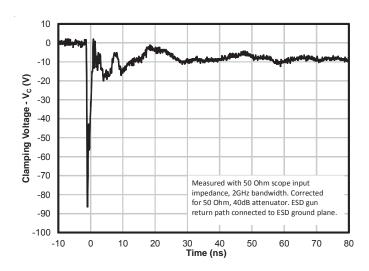
Junction Capacitance vs. Reverse Voltage (Between any I/O and Ground)



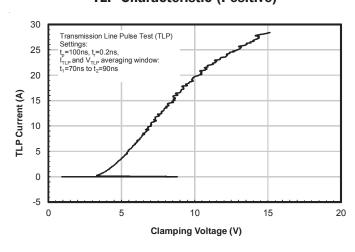
ESD Clamping (+8kV Contact per IEC 61000-4-2) (Between any I/O and Ground)



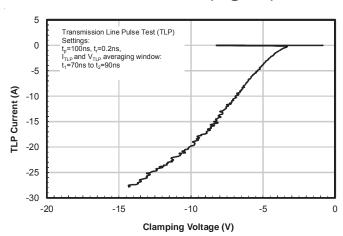
ESD Clamping (-8kV Contact per IEC 61000-4-2) (Between any I/O and Ground)



TLP Characteristic (Positive)



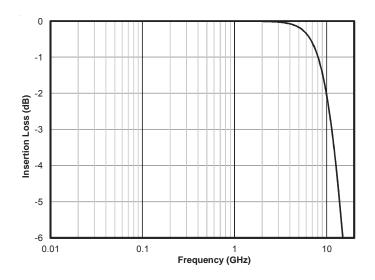
TLP Characteristic (Negative)



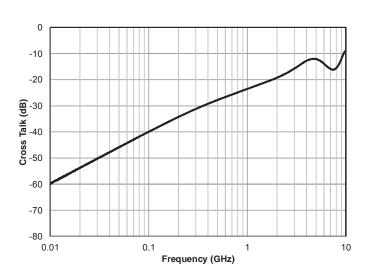


Typical Characteristics

Typical Insertion Loss S21



Analog Crosstalk

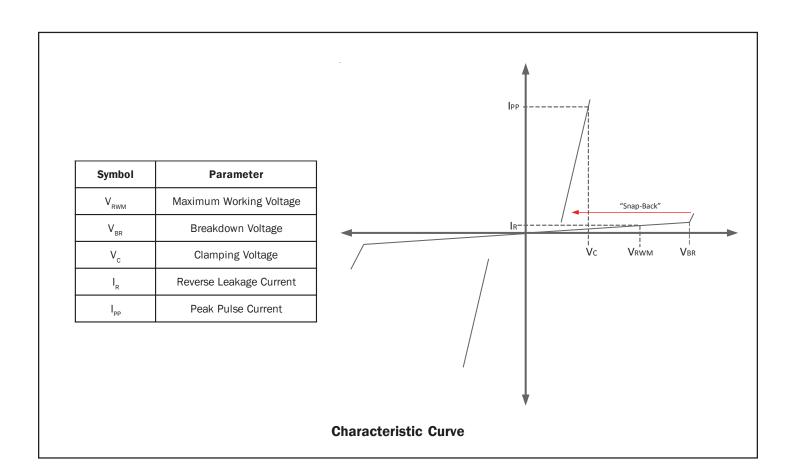




Applications Information

Device Operation

This device utilizes a multi-junction structure that is designed to switch to a low voltage state when triggered by ESD, EOS, or other transient events. During normal operation, the device will present a highimpedance to the circuit for voltage up to the working voltage $(V_{\scriptscriptstyle RWM})$ of the device. When the voltage across the device terminals exceeds the breakdown voltage $(V_{\mbox{\tiny RR}})$, avalanche breakdown occurs in the blocking junction causing the device to "snap-back" or switch to a low impedance on-state. This has the advantage of lowering the overall clamping voltage (V_c) as ESD peak pulse current (I_{pp}) flows through the device. Once the current subsides, the device will return to a highimpedance off-state. Since this device is bidirectional, it will behave the same way for positive or negative polarity transient events.



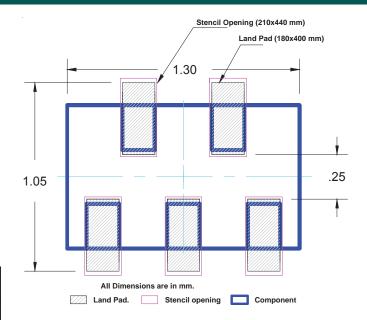


Applications Information

Assembly Guidelines

The small size of this device means that some care must be taken during the mounting process to insure reliable solder joint. The table below provides Semtech's recommended assembly guidelines for mounting this device. The figure at the right details Semtech's recommended aperture based on the below recommendations. Note that these are only recommendations and should serve only as a starting point for design since there are many factors that affect the assembly process. The exact manufacturing parameters will require some experimentation to get the desired solder application.

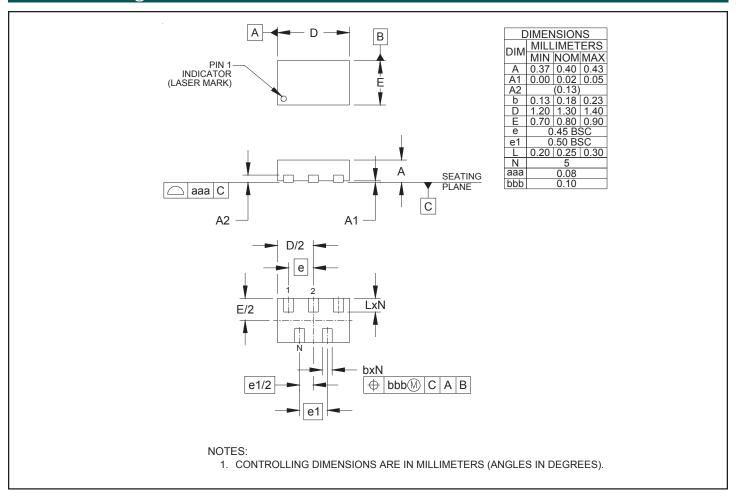
Assembly Parameter	Recommendation		
Solder Stencil Design	Laser cut, Electro-polished		
Aperture shape	Rectangular		
Solder Stencil Thickness	0.100 mm (0.004")		
Solder Paste Type	Type 4 size sphere or smaller		
Solder Reflow Profile	Per JEDEC J-STD-020		
PCB Solder Pad Design	Non-Solder mask defined		
PCB Pad Finish	OSP OR NiAu		



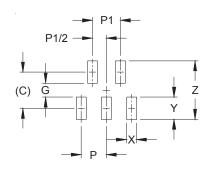
Recommended Mounting Pattern



Outline Drawing - SLP1308N5T



Land Pattern - SLP1308N5T



DIMENSIONS		
DIM	MILLIMETERS	
С	(0.65)	
G	0.25	
Р	0.45	
P1	0.50	
Χ	0.18	
Υ	0.40	
Ζ	1.05	

NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.



Marking Code



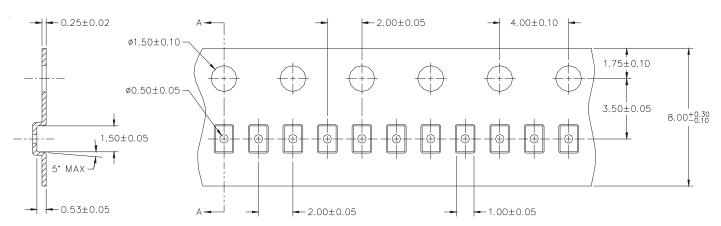
YYWW = Date Code Dot indicates pin 1

Ordering Information

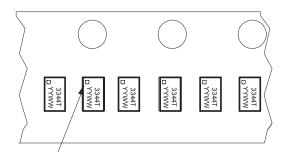
Part Number	Qty per Reel	Reel Size	
RClamp3344T.TNT	10,000	7 Inch	

RailClamp and RClamp are trademarks of Semtech Corporation.

Carrier Tape Specification



SECTION A-A



Pin 1 Location (Towards Sprocket Holes)

User Direction of feed

Device Orientation in Tape



Contact Information

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